

# OPA9425

## Infrared LED Chip

GaAs /GaAs

**1.Material** Substrate GaAs (N Type)  
Epitaxial Layer GaAs (P/N Type)

**2.Electrode** N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy

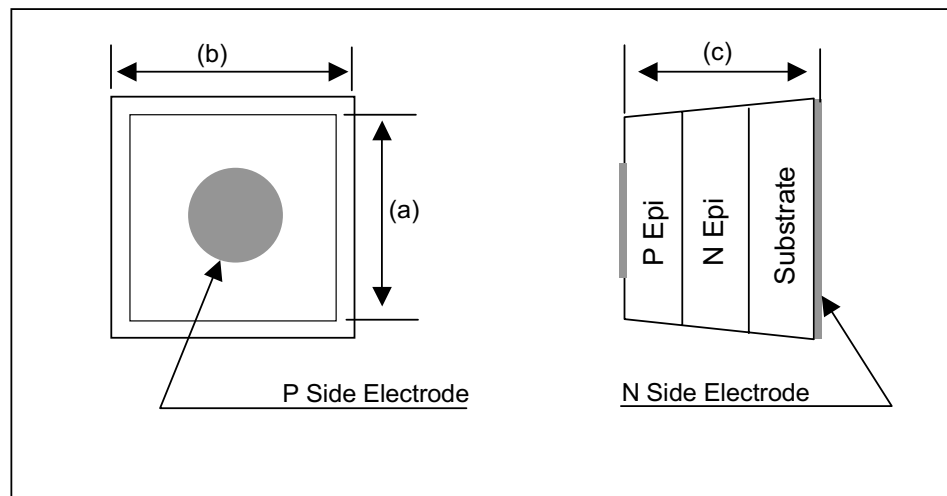
### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.3		V	$I_F=20\text{mA}$
	$V_{F(2)}$		1.5	1.7	V	$I_F=100\text{mA}$
Reverse Voltage	$V_R$	5.0	20		V	$I_R=10\mu\text{A}$
Power	$P_{O(1)}$		5		mW	$I_F=20\text{mA}$
	$P_{O(2)}$	7	12		mW	$I_F=100\text{mA}$
Wavelength	$\lambda_P$		940		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		45		nm	$I_F=20\text{mA}$

Note : Assembled into T1<sup>3</sup>/<sub>4</sub> plastic package.

### 4. Mechanical Data

- (a) Emission Area ----- 8mil × 8mil
- (b) Bottom Area ----- 10mil × 10mil
- (c) Chip Thickness ----- 9mil



Knowledge\*on Inc.

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